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N-Channel UniFETTM FRFET[®] MOSFET 500 V, 24 A, 200 m Ω

Features

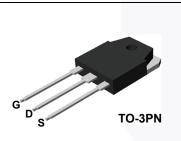
- + $R_{DS(on)}$ = 166 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 12 A
- Low Gate Charge (Typ. 65 nC)
- Low C_{rss} (Typ. 32 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

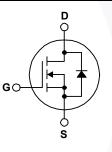
Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFET[™] MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET[®] MOSFET has been enhanced by lifetime control. Its trr is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp balasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		FDA24N50F	Unit			
V _{DSS}	Drain to Source Voltage			500	V	
V _{GSS}	Gate to Source Voltage			±30	V	
I _D	Drain Current	- Continuous (T _C = 25 ^o C)		24		
		- Continuous (T _C = 100 ^o C)		14	Α	
I _{DM}	Drain Current	- Pulsed ((Note 1)	96	А	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			1872	mJ	
I _{AR}	Avalanche Current		(Note 1)	24	Α	
E _{AR}	Repetitive Avalanche Ener	ду	(Note 1)	27	mJ	
dv/dt	Peak Diode Recovery dv/dt			20	V/ns	
P _D	David Diasia di sa	(T _C = 25°C)		270	W	
	Power Dissipation	- Derate Above 25°C		2.2	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

Thermal Characteristics

Symbol	Parameter	FDA24N50F	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.46	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient, Max.	40	- °C/W

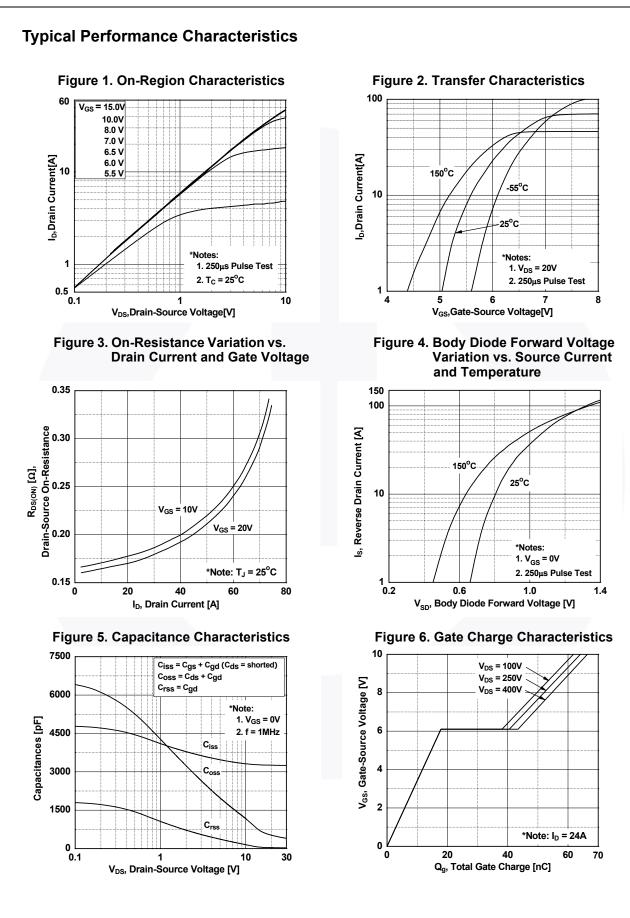
FDA24N50F — N-Channel UniFETTM FRFET[®] MOSFET

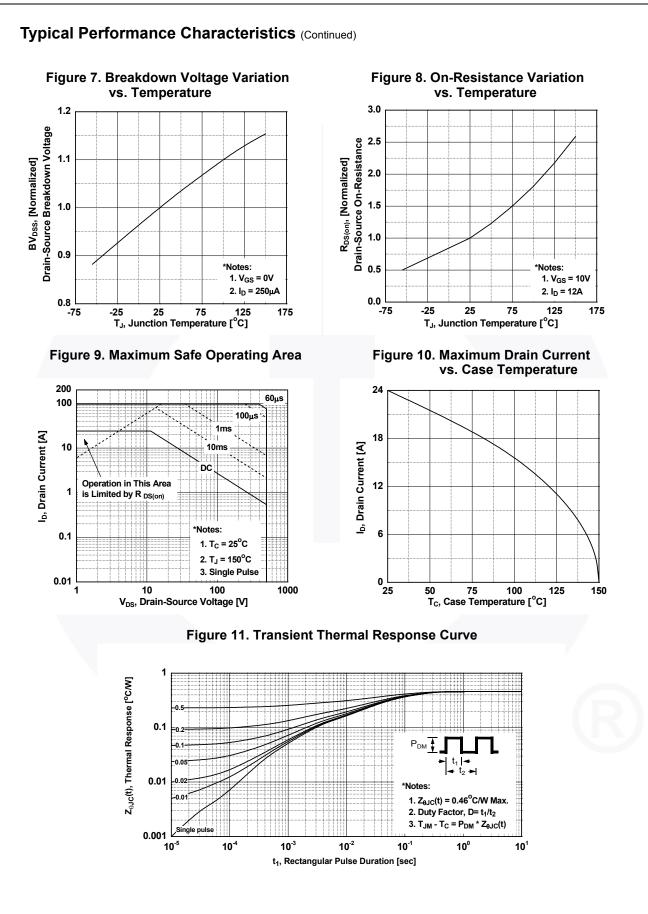
May 2014

		Top Mark	Package	Packing Method	Reel Size	e Ta	ape Width	Qua	antity
		TO-3PN			N/A		30 units		
Electrica	l Chara	acteristics T _C = 25°C	unless other	wise noted.					
Symbol		Parameter		Test Condition	s	Min.	Тур.	Max.	Unit
Off Charac	teristics		P						
BV _{DSS}	Drain to Source Breakdown Voltage		1	1 - 250 + 0.14 = 0.14 = -25%			-	-	V
∆BV _{DSS}	Breakdown Voltage Temperature Coefficient			$I_D = 250 \ \mu\text{A}, \ V_{GS} = 0 \ V, \ T_J = 25^{\circ}\text{C}$ $I_D = 250 \ \mu\text{A}, \ \text{Referenced to } 25^{\circ}\text{C}$			-	-	
ΔDV_{DSS}			I _D =				0.6	-	V/ºC
	7 0 1			V _{DS} = 500 V, V _{GS} = 0 V		-	-	1	-
I _{DSS} Zero		o Gate Voltage Drain Current		$V_{DS} = 400 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$			-	10	μA
I _{GSS}	Gate to Body Leakage Current		V _G s	$_{\rm S} = \pm 30 \text{ V}, \text{ V}_{\rm DS} = 0 \text{ V}$		-	-	±100	nA
On Charac	teristics								
V _{GS(th)}	Gate Th	reshold Voltage	VG	_S = V _{DS} , I _D = 250 μA		3.0	-	5.0	V
R _{DS(on)}		ain to Source On Resistance	-	$_{\rm S} = 10$ V, $I_{\rm D} = 12$ A		-	0.166	0.2	Ω
9 _{FS}	Forward	Transconductance		_S = 20 V, I _D = 12 A		-	30	-	S
Dynamic C	haracte	ristics							
C _{iss}	Input Capacitance					-	3240	4310	pF
C _{oss}		apacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		-	450	600	p. pF
C _{rss}		Transfer Capacitance	f =			-	32	48	pF
Q _{g(tot)}		te Charge at 10V	V	- 400 \/ - 24 A			65	85	nC
Q _{gs}		Source Gate Charge		$V_{DS} = 400 \text{ V}, \text{ I}_{D} = 24 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4,)			18	-	nC
Q _{gd}		Drain "Miller" Charge	• 63			-	26	-	nC
Switching									
-							40	109	
t _{d(on)}		Delay Time Rise Time	Vor	V_{DD} = 250 V, I _D = 24 A, V _{GS} = 10 V, R _G = 25 Ω		-	49	108	ns
t _r						•	105	220	ns
t _{d(off)}		Delay Time Fall Time					165 87	340 185	ns ns
t _f					(Note 4)	-	07	105	115
		e Characteristics	o Diada For	word Current		-		24	^
I _S	Maximum Continuous Drain to Source Dio						-	24 96	A
I _{SM}		Maximum Pulsed Drain to Source Diode For Drain to Source Diode Forward Voltage		$V_{GS} = 0 \text{ V}, \text{ I}_{SD} = 24 \text{ A}$			-	90 1.4	A V
V _{SD}		Recovery Time				-	- 264	1.4	-
t _{rr} Q _{rr}		Recovery Charge		V _{GS} = 0 V, I _{SD} = 24 A, dI _F /dt = 100 A/μs			1.4		ns μC
œrr	11070100	Receivery charge	F.				1.4		μΟ

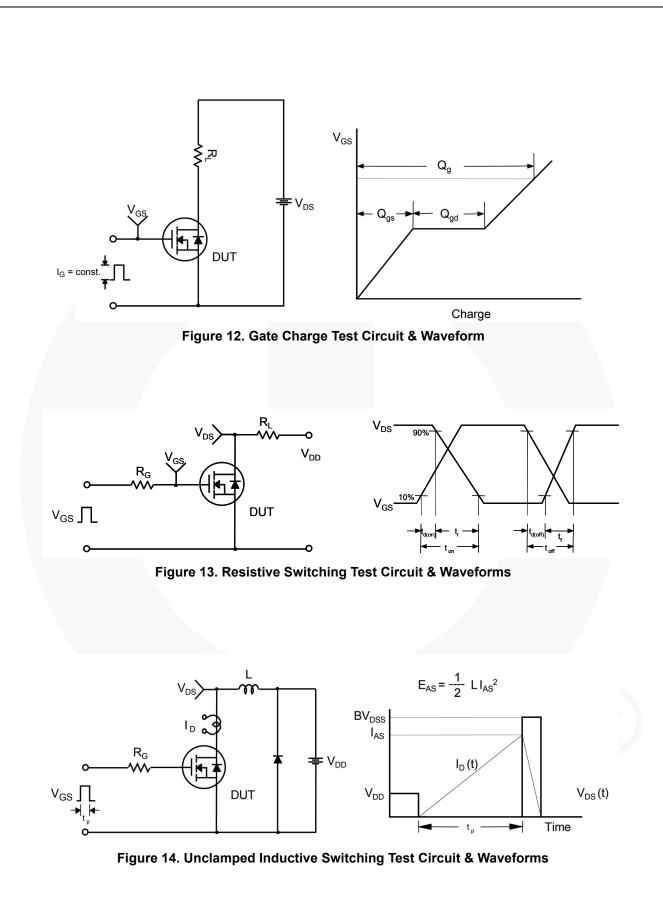
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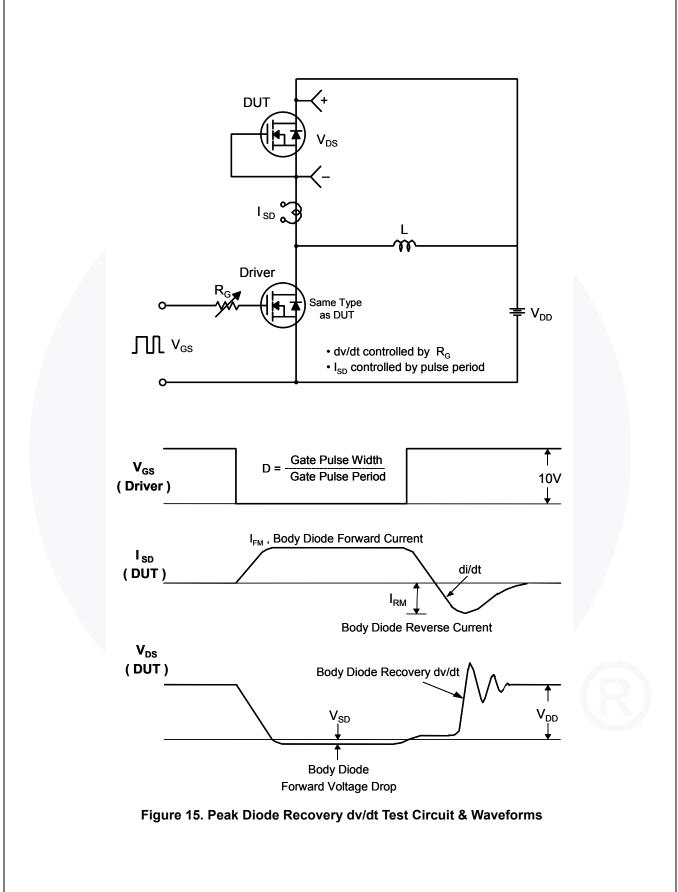




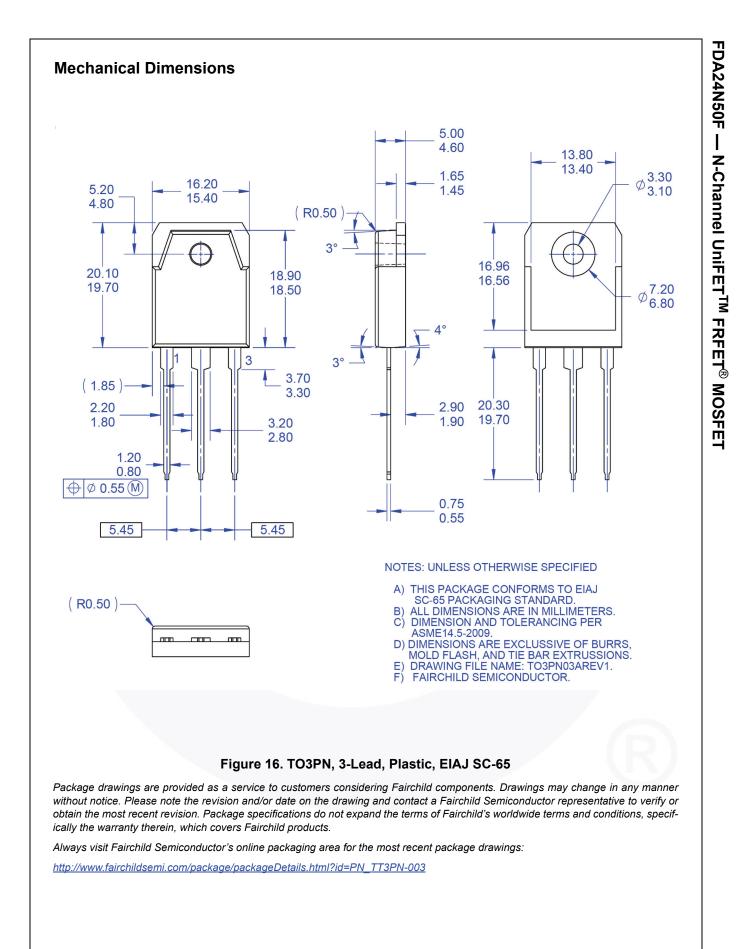
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